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June 2014

# **FQA170N06**

# N-Channel QFET® MOSFET 60 V, 170 A, 5.6 mΩ

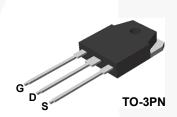
# **Description**

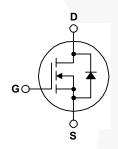
This N-Channel enhancement mode power MOSFET is • 170 A, 60 V,  $R_{DS(on)}$  = 5.6 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 220 nC) resistance, and to provide superior switching performance and • Low Crss (Typ. 620 pF) high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor • 100% Avalanche Tested control, and variable switching power applications.

### **Features**

- $I_D = 85 A$

- · 175°C Maximum Junction Temperature Rating





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQA170N06	Unit
$V_{DSS}$	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		170	Α
	- Continuous (T <sub>C</sub> = 100°C)		120	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	680	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		990	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	170	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note		7.0	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		375	W
	- Derate above 25°C	2.5	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.	300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FQA170N06	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA170N06	FQA170N06	TO-3PN	Tube	N/A	N/A	30 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	;	0.053		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μА
		V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 85 A		0.0045	0.0056	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 85 A		85		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		7200	9350	pF
C <sub>oss</sub>	Output Capacitance			3100	4000	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			620	810	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V - 20 V I - 95 A		85	180	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_{D} = 85 \text{ A},$ $R_{G} = 25 \Omega$		700	1400	ns
$t_{d(off)}$	Turn-Off Delay Time			260	530	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4	)	430	870	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 170 A,		220	290	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		50		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4		100		nC
	ource Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current (Note 5)				170	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				680	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 170 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 170 A,		100		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>E</sub> / dt = 100 A/μs		315	//	nC

- Notes: 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 40  $\mu$ H, I<sub>AS</sub> = 170 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  170 A, di/dt  $\leq$  300  $\lambda$ / $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature. 5. Continuous drain current calculated by maximum Jjnction temperature: limited by package.

# **Typical Characteristics**

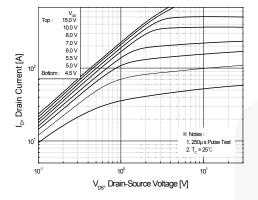


Figure 1. On-Region Characteristics.

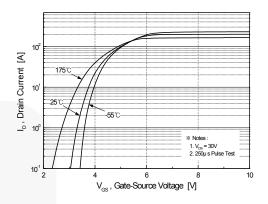


Figure 2. Transfer Characteristics.

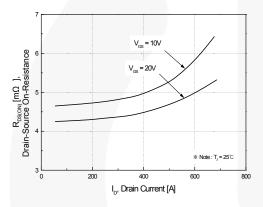


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage.

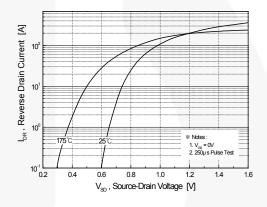


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature.

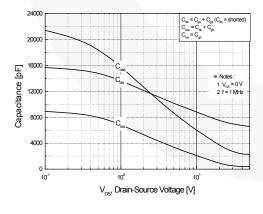


Figure 5. Capacitance Characteristics.

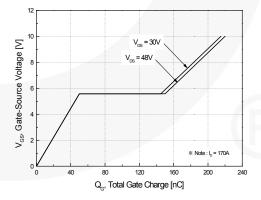


Figure 6. Gate -Charge Characteristics.

# Typical Characteristics (Continued)

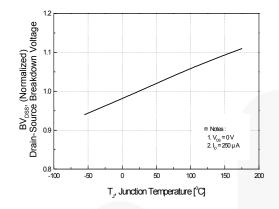


Figure 7. Breakdown Voltage Variation vs Temperature.

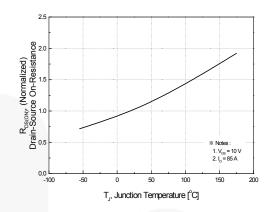


Figure 8. On-Resistance Variation vs Temperature.

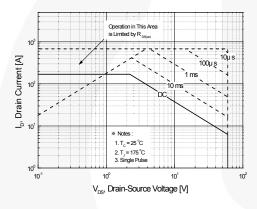


Figure 9. Maximum Safe Operating Area.

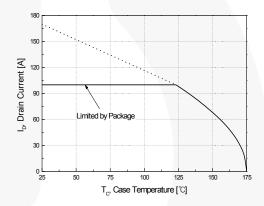


Figure 10. Maximum Drain Current vs Case Temperature.

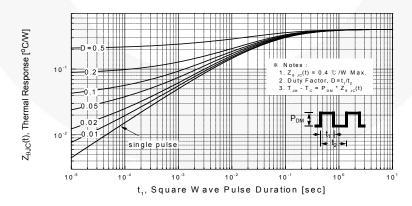


Figure 11. Transient Thermal Response Curve.

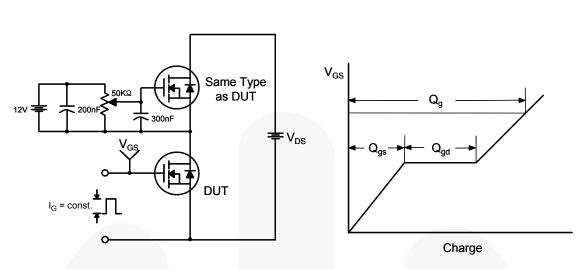


Figure 12. Gate Charge Test Circuit & Waveform

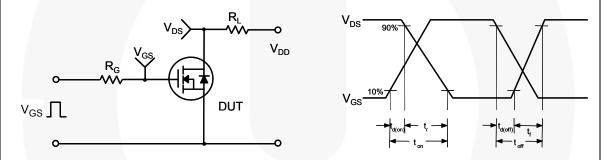


Figure 13. Resistive Switching Test Circuit & Waveforms

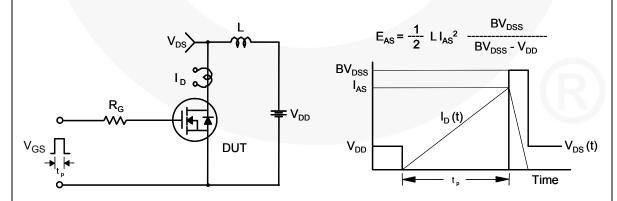
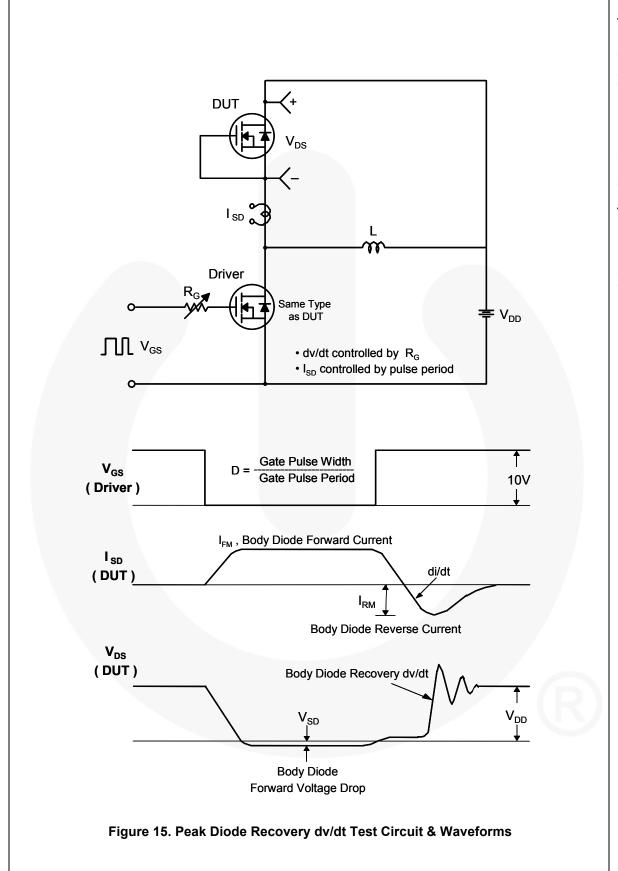
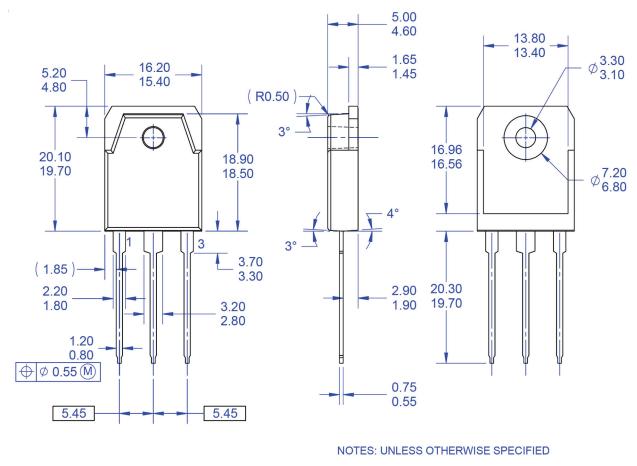
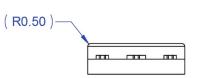


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD. B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
  DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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